

Silicon NPN Power Transistors

2SD425 2SD426

**DESCRIPTION**

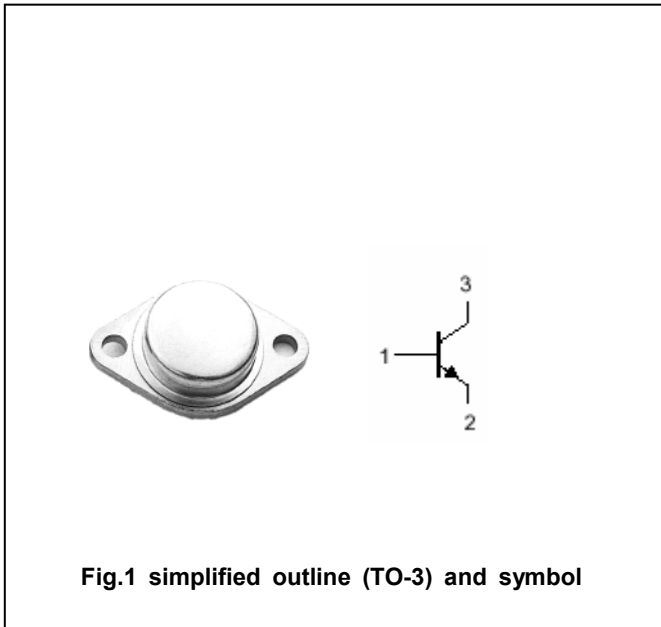
- With TO-3 package
- Complement to type 2SB555/556
- High power dissipation

**APPLICATIONS**

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	2SD425	140	V
		2SD426	120	
V <sub>CEO</sub>	Collector-emitter voltage	2SD425	140	V
		2SD426	120	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		12	A
I <sub>E</sub>	Emitter current		12	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25□	100	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-65~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SD425	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	140			V
		2SD426		120			
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage		I <sub>E</sub> =10mA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	2SD425	I <sub>C</sub> =7A ; I <sub>B</sub> =0.7A			3.0	V
		2SD426	I <sub>C</sub> =6A ; I <sub>B</sub> =0.6A				
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =7A ; V <sub>CE</sub> =5V			2.5	V
I <sub>CBO</sub>	Collector cut-off current		V <sub>CB</sub> =50V ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =5V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain		I <sub>C</sub> =2A ; V <sub>CE</sub> =5V	40		140	
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =2A ; V <sub>CE</sub> =5V		5		MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)